

FMC03N60E

FUJI POWER MOSFET

Super FAP-E³ series

N-CHANNEL SILICON POWER MOSFET

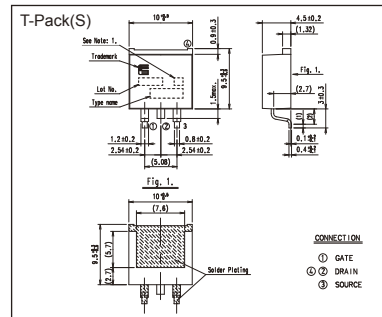
■ Features

- Maintains both low power loss and low noise
- Lower $R_{DS(on)}$ characteristic
- More controllable switching dv/dt by gate resistance
- Smaller V_{GS} ringing waveform during switching
- Narrow band of the gate threshold voltage ($3.0 \pm 0.5V$)
- High avalanche durability

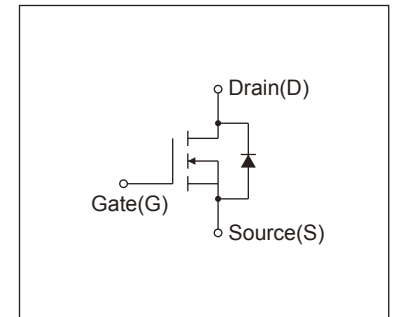
■ Applications

- Switching regulators
- UPS (Uninterruptible Power Supply)
- DC-DC converters

■ Outline Drawings [mm]



■ Equivalent circuit schematic



■ Maximum Ratings and Characteristics

● Absolute Maximum Ratings at $T_c=25^\circ C$ (unless otherwise specified)

Description	Symbol	Characteristics	Unit	Remarks
Drain-Source Voltage	V_{DS}	600	V	
	V_{DSX}	600	V	$V_{GS} = -30V$
Continuous Drain Current	I_D	± 3	A	
Pulsed Drain Current	I_{DP}	± 12	A	
Gate-Source Voltage	V_{GS}	± 30	V	
Repetitive and Non-Repetitive Maximum Avalanche Current	I_{AR}	3	A	Note*1
Non-Repetitive Maximum Avalanche Energy	E_{AS}	237	mJ	Note*2
Repetitive Maximum Avalanche Energy	E_{AR}	6.0	mJ	Note*3
Peak Diode Recovery dV/dt	dV/dt	4.2	kV/ μs	Note*4
Peak Diode Recovery $-di/dt$	$-di/dt$	100	A/ μs	Note*5
Maximum Power Dissipation	P_D	1.67	W	$T_a=25^\circ C$
		60		$T_c=25^\circ C$
Operating and Storage Temperature range	T_{ch}	150	$^\circ C$	
	T_{stg}	-55 to + 150	$^\circ C$	

● Electrical Characteristics at $T_c=25^\circ C$ (unless otherwise specified)

Description	Symbol	Conditions	min.	typ.	max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$I_D=250\mu A, V_{GS}=0V$	600	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$I_D=250\mu A, V_{DS}=V_{GS}$	2.5	3.0	3.5	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=600V, V_{GS}=0V$	-	-	25	μA
		$V_{DS}=480V, V_{GS}=0V$	-	-	250	
Gate-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 30V, V_{DS}=0V$	-	10	100	nA
Drain-Source On-State Resistance	$R_{DS(on)}$	$I_D=1.5A, V_{GS}=10V$	-	1.966	2.30	Ω
Forward Transconductance	g_{fs}	$I_D=1.5A, V_{DS}=25V$	1.75	3.5	-	S
Input Capacitance	C_{iss}	$V_{DS}=25V$	-	610	915	pF
Output Capacitance	C_{oss}	$V_{GS}=0V$	-	59	88.5	
Reverse Transfer Capacitance	C_{rss}	$f=1MHz$	-	4.5	6.8	
Turn-On Time	$t_d(on)$	$V_{cc}=300V$	-	7	10.5	ns
	t_r	$V_{GS}=10V$	-	7.5	11.3	
Turn-Off Time	$t_d(off)$	$I_D=1.5A$	-	51	76.5	
	t_f	$R_G=27\Omega$	-	16	24.0	
Total Gate Charge	Q_G	$V_{cc}=300V$	-	21.5	32	nC
Gate-Source Charge	Q_{GS}	$I_D=3A$	-	5.5	8	
Gate-Drain Charge	Q_{GD}	$V_{GS}=10V$	-	6	9	
Avalanche Capability	I_{AV}	$L=19.3mH, T_{ch}=25^\circ C$	3	-	-	A
Diode Forward On-Voltage	V_{SD}	$I_F=3A, V_{GS}=0V, T_{ch}=25^\circ C$	-	0.86	1.30	V
Reverse Recovery Time	t_{rr}	$I_F=3A, V_{GS}=0V$	-	0.38	-	μs
Reverse Recovery Charge	Q_{rr}	$-di/dt=100A/\mu s, T_{ch}=25^\circ C$	-	1.8	-	μC

● Thermal Characteristics

Description	Symbol	Test Conditions	min.	typ.	max.	Unit
Thermal resistance	$R_{th(ch-c)}$	Channel to Case			1.200	$^\circ C/W$
	$R_{th(ch-a)}$	Channel to Ambient			62.0	$^\circ C/W$

Note *1 : $T_{ch} \leq 150^\circ C$

Note *2 : Stating $T_{ch}=25^\circ C, I_{AS}=1.2A, L=302mH, V_{cc}=60V, R_G=50\Omega$
 E_{AS} limited by maximum channel temperature and avalanche current.
 See to 'Avalanche Energy' graph.

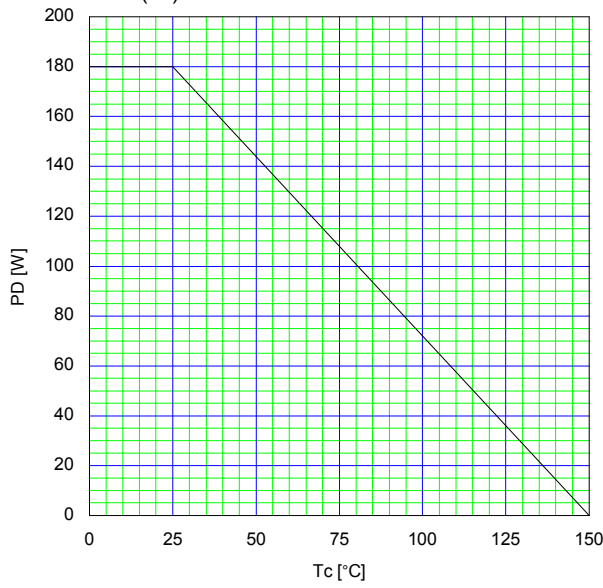
Note *3 : Repetitive rating : Pulse width limited by maximum channel temperature.

See to the 'Transient Thermal Impedance' graph.

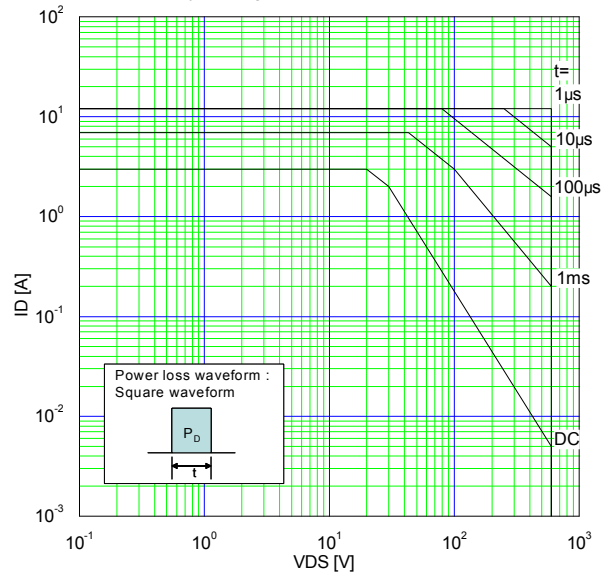
Note *4 : $I_F \leq I_D, -di/dt=100A/\mu s, V_{cc} \leq BV_{DSS}, T_{ch} \leq 150^\circ C$.

Note *5 : $I_F \leq I_D, dv/dt=4.2kV/\mu s, V_{cc} \leq BV_{DSS}, T_{ch} \leq 150^\circ C$.

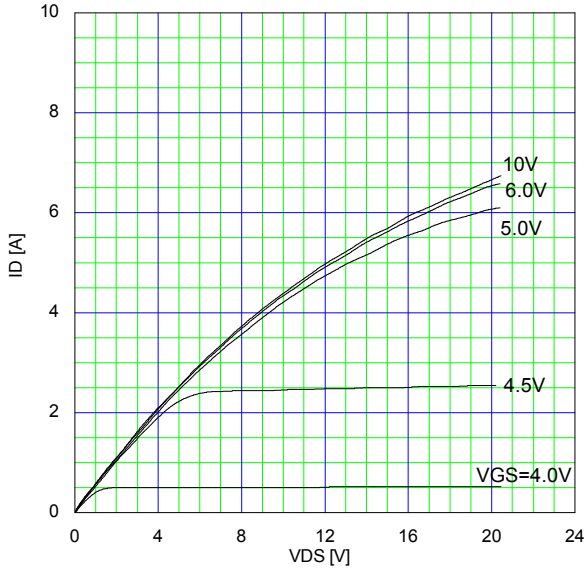
Allowable Power Dissipation
 $PD=f(T_c)$



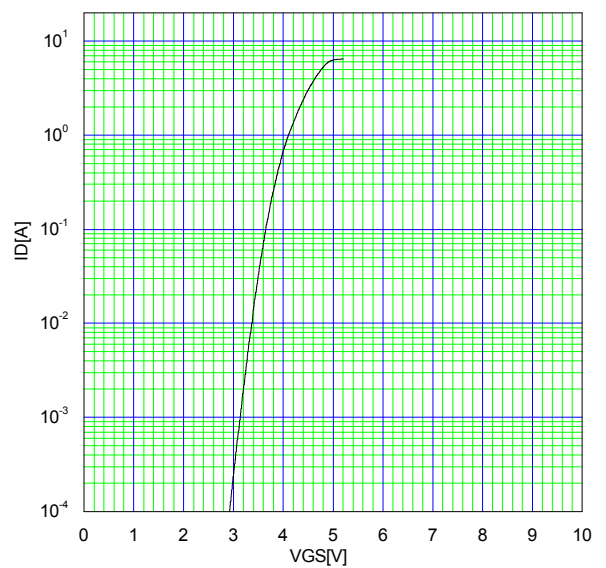
Safe Operating Area
 $I_D=f(V_{DS}): \text{Duty}=0(\text{Single pulse}), T_c=25^\circ\text{C}$



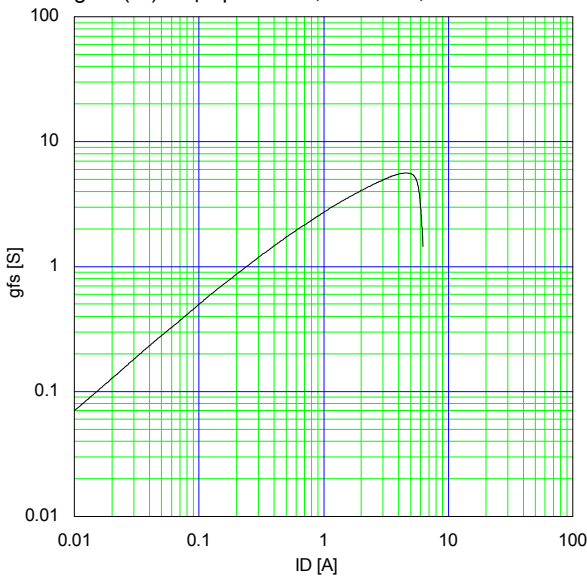
Typical Output Characteristics
 $I_D=f(V_{DS}): 80 \mu\text{s pulse test}, T_{ch}=25^\circ\text{C}$



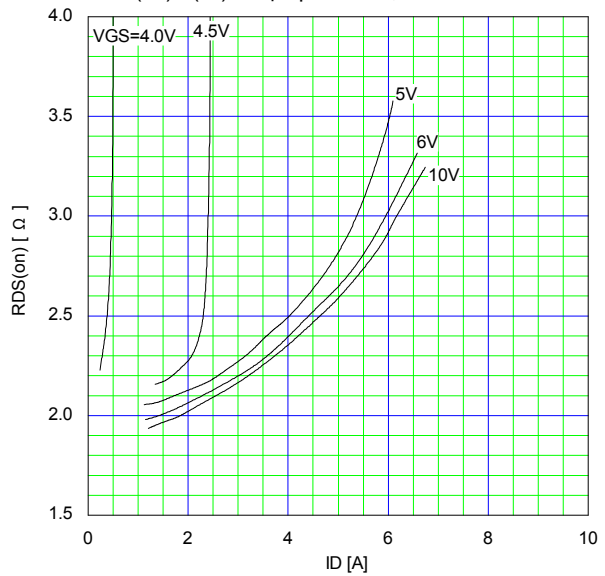
Typical Transfer Characteristic
 $I_D=f(V_{GS}): 80 \mu\text{s pulse test}, V_{DS}=25\text{V}, T_{ch}=25^\circ\text{C}$



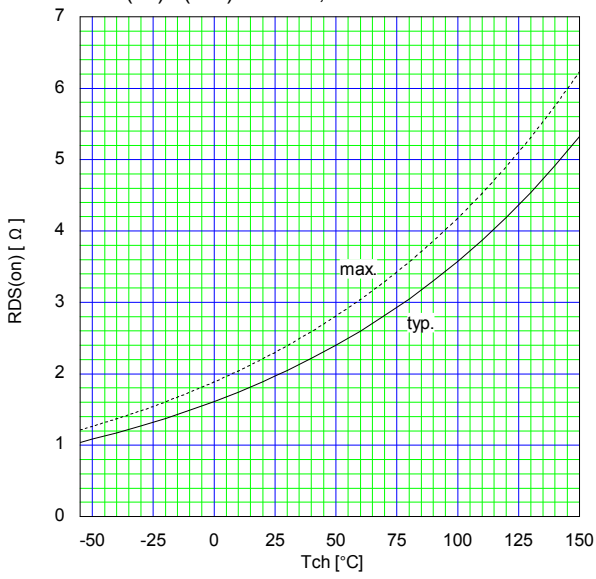
Typical Transconductance
 $g_{fs}=f(I_D): 80 \mu\text{s pulse test}, V_{DS}=25\text{V}, T_{ch}=25^\circ\text{C}$



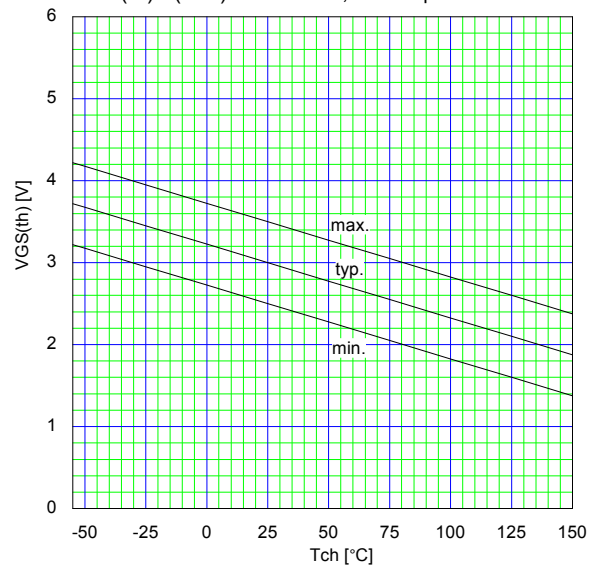
Typical Drain-Source on-state Resistance
 $R_{DS(on)}=f(I_D): 80 \mu\text{s pulse test}, T_{ch}=25^\circ\text{C}$



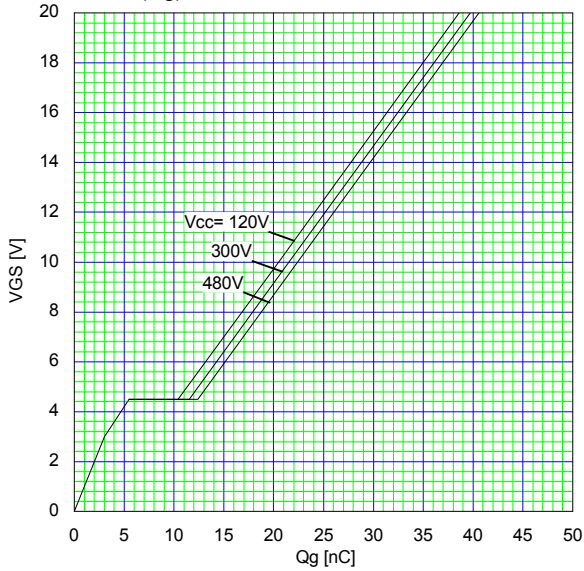
Drain-Source On-state Resistance
 $R_{DS(on)}=f(T_{ch}):I_D=1.5A, V_{GS}=10V$



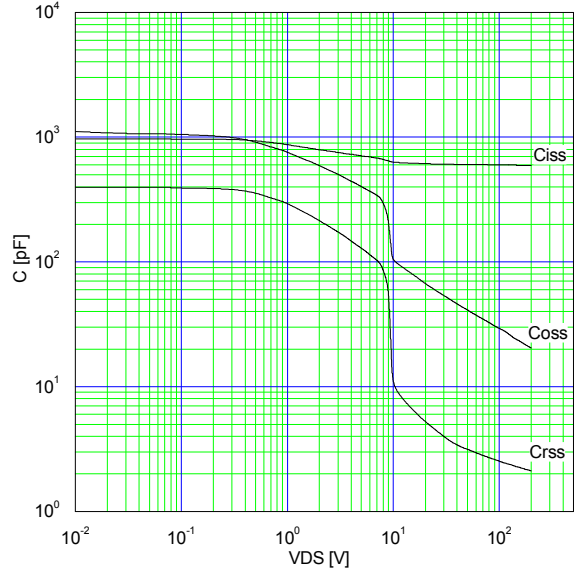
Gate Threshold Voltage vs. T_{ch}
 $V_{GS(th)}=f(T_{ch}):V_{DS}=V_{GS}, I_D=250\mu A$



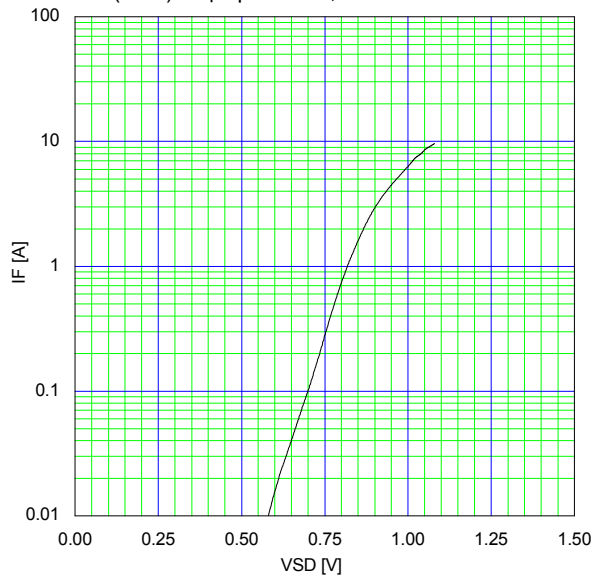
Typical Gate Charge Characteristics
 $V_{GS}=f(Q_g):I_D=3A, T_{ch}=25^\circ C$



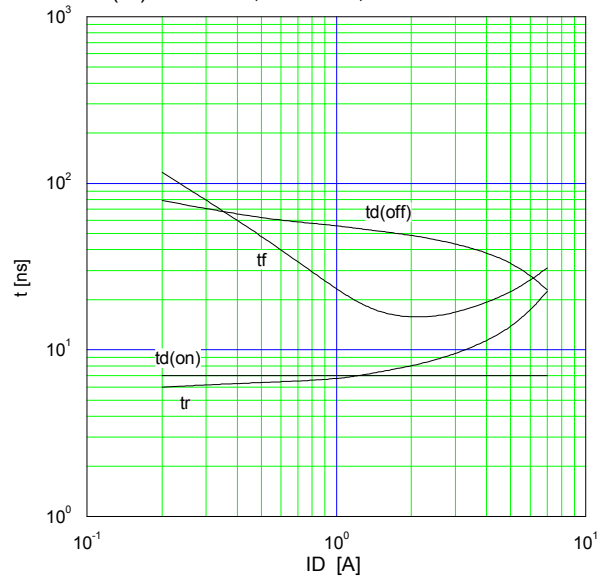
Typical Capacitance
 $C=f(V_{DS}):V_{GS}=0V, f=1MHz$

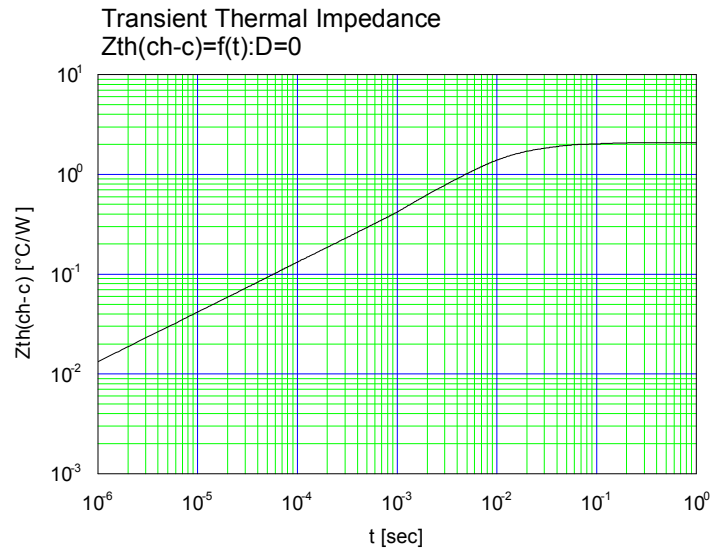
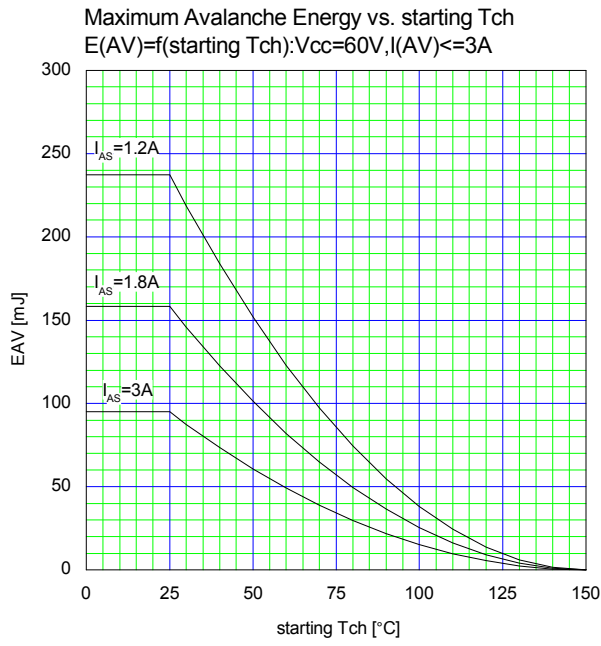


Typical Forward Characteristics of Reverse Diode
 $I_F=f(V_{SD}):80\mu s \text{ pulse test}, T_{ch}=25^\circ C$



Typical Switching Characteristics vs. ID
 $t=f(I_D):V_{cc}=300V, V_{GS}=10V, R_G=27\Omega$





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